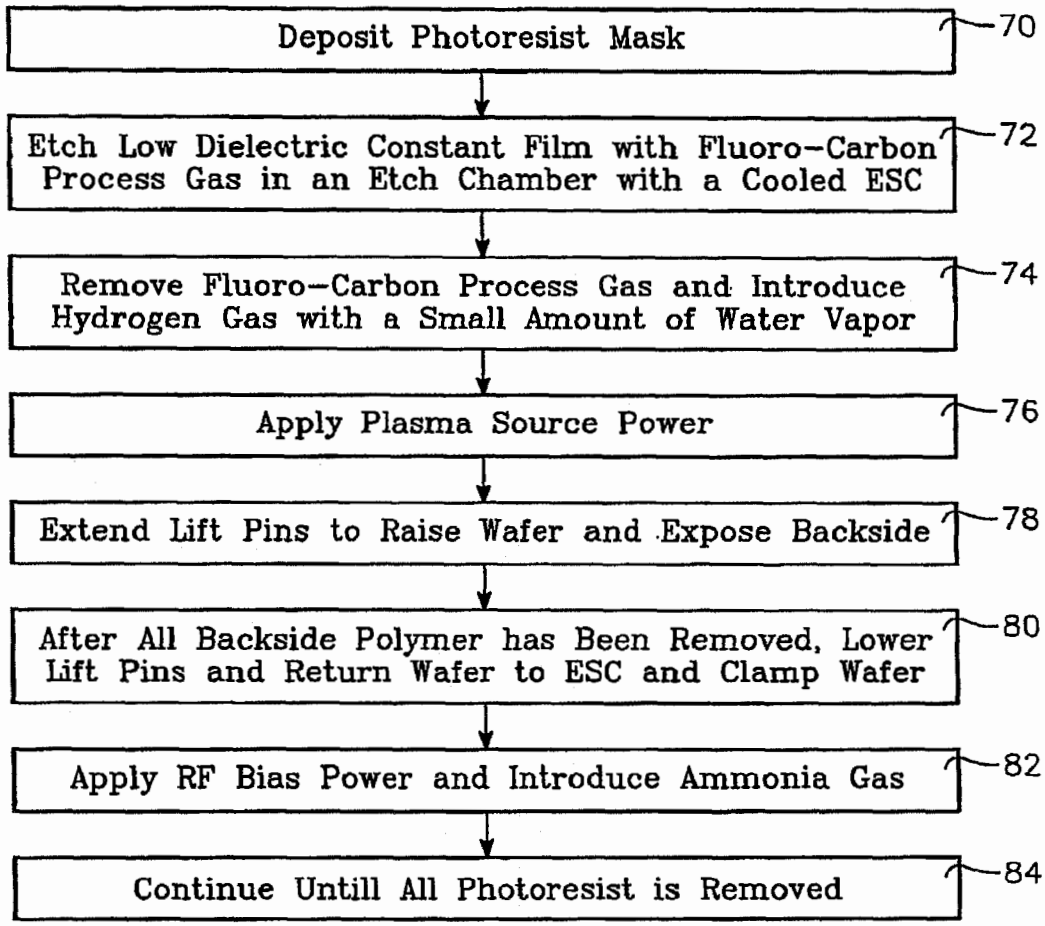

Deposit Photoresist Mask
70
Etch Low Dielectric Constant Film with Fluoro-Carbon Process Gas in an Etch Chamber with a Cooled ESC
72
Remove Fluoro-Carbon Process Gas and Introduce Hydrogen Gas with a Small Amount of Water Vapor
74
Apply Plasma Source Power
76
Extend Lift Pins to Raise Wafer and Expose Backside
78
After All Backside Polymer has Been Removed, Lower Lift Pins and Return Wafer to ESC and Clamp Wafer
80
Apply RF Bias Power and Introduce Ammonia Gas
82
Continue Untill All Photoresist is Removed
84

FIG. 1

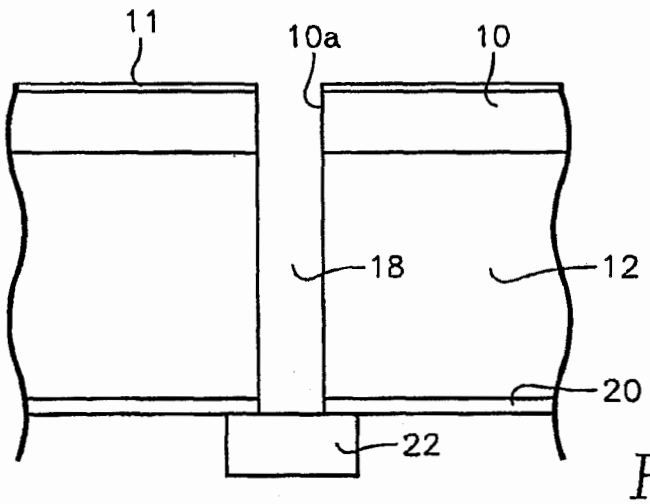

11
10a
10
18
12
20
22

FIG. 2

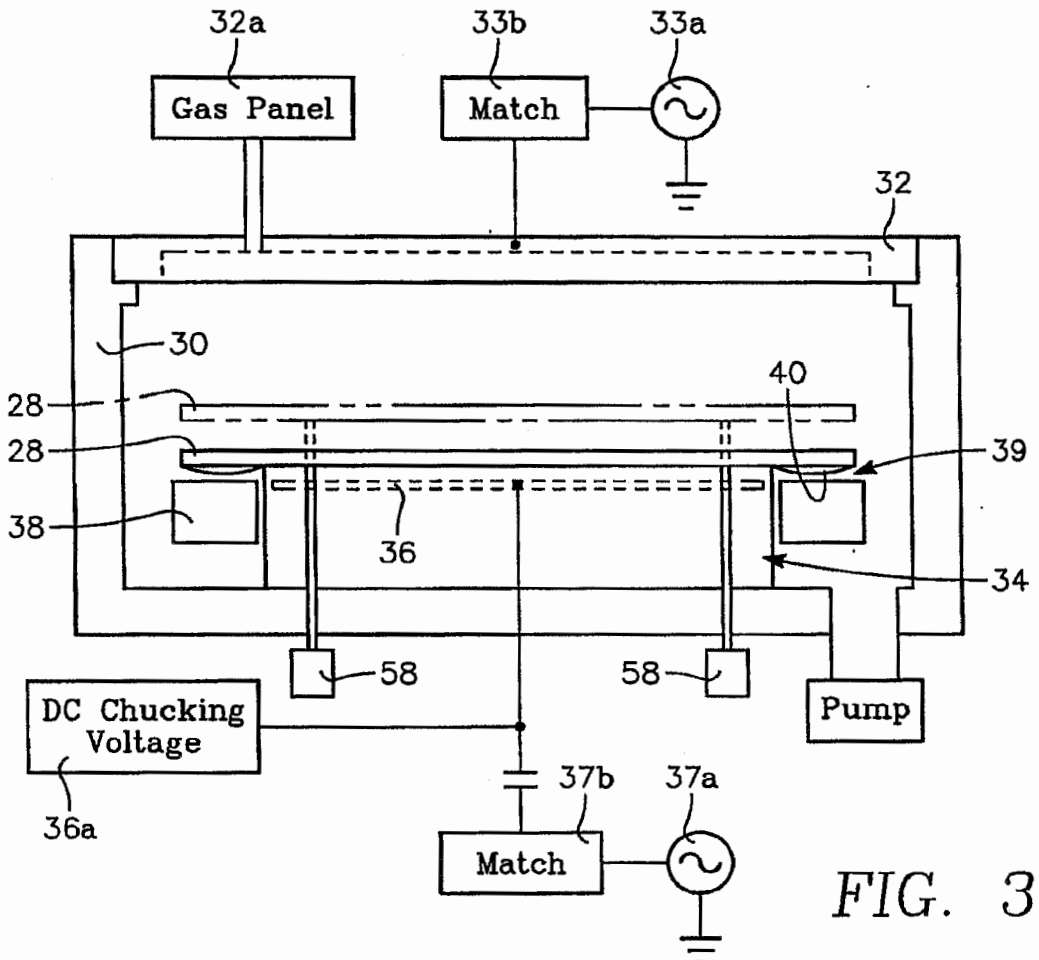

32a
33b
33a
Gas Panel
Match
32
30
40
28
28
39
38
36
34
58
58
DC Chucking Voltage
Pump
37b
37a
36a
Match

FIG. 3

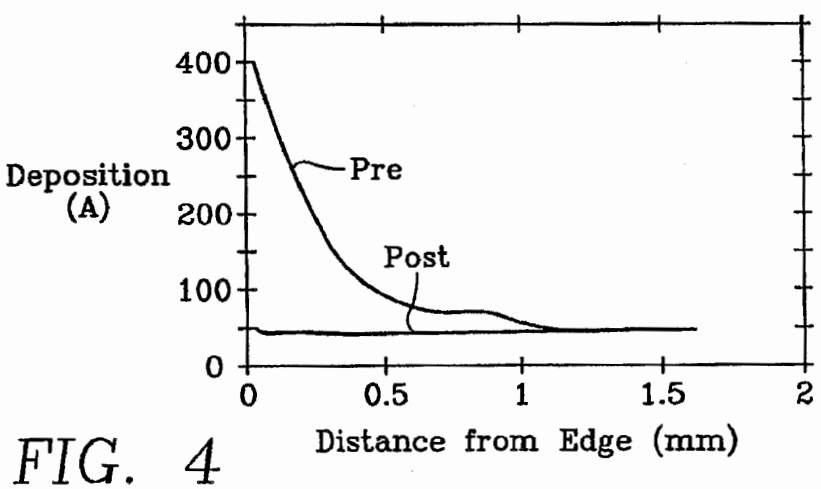

400
300
200
100
0
Deposition (A)
Pre
Post
0
0.5
1
1.5
2
Distance from Edge (mm)

FIG. 4